

PATENT ASSIGNMENT

Electronic Version v1.1
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SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT
CONVEYING PARTY DATA	
Name	Execution Date
SanDisk Corporation	04/04/2011
RECEIVING PARTY DATA	
Name:	SanDisk Technologies Inc.
Street Address:	6900 North Dallas Parkway
Internal Address:	Two Legacy Town Center
City:	Plano
State/Country:	TEXAS
Postal Code:	75024
PROPERTY NUMBERS Total: 1	
Property Type	Number
Patent Number:	7301805
CORRESPONDENCE DATA	
Fax Number:	(408)801-8512
<i>Correspondence will be sent via US Mail when the fax attempt is unsuccessful.</i>	
Phone:	4088012863
Email:	simona.benjamin@sandisk.com
Correspondent Name:	SanDisk Corporation
Address Line 1:	601 Mccarthy Boulevard
Address Line 2:	Patent Department/Simona Benjamin
Address Line 4:	Milpitas, CALIFORNIA 95035
ATTORNEY DOCKET NUMBER:	SDK0521.001US
NAME OF SUBMITTER:	Simona Benjamin
Total Attachments: 5 source=page 55#page1.tif source=page 55#page2.tif source=page 55#page3.tif source=page 55#page4.tif source=page 55#page5.tif	

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ASSIGNMENT

WHEREAS, SanDisk Corporation, a Delaware corporation, doing business at 601 McCarthy Boulevard, Milpitas, CA 95035 (hereinafter referred to as **ASSIGNOR**), holds right, title and interest throughout the world in and to the patents and patent applications set forth in the attached Exhibit A, together with all divisions, continuations, or continuations-in-part thereof, and all patents issuing thereon including reissues, renewals, substitutions, re-examinations and extensions thereof, and any and all corresponding foreign patents and patent applications (hereinafter referred to as, collectively, **THE ASSIGNED PATENT RIGHTS**);

WHEREAS, SanDisk Technologies Inc., a Texas corporation, doing business at Two Legacy Town Center, 6900 North Dallas Parkway, Plano, Texas 75024, (hereinafter referred to as **ASSIGNEE**), is desirous of acquiring the full and exclusive right, title and interest in **THE ASSIGNED PATENT RIGHTS**;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, **ASSIGNOR** hereby assigns, transfers and conveys unto the said **ASSIGNEE**, and **ASSIGNEE** accepts, all of **ASSIGNOR**'s right, title and interest throughout the world in and to **THE ASSIGNED PATENT RIGHTS** and to all Letters Patent or applications or similar legal protection, not only in the United States and its territorial possessions, but in all countries foreign thereto to be obtained for **THE ASSIGNED PATENT RIGHTS**, and to any continuation, division, renewal, substitute or reissue thereof or any legal equivalent thereof in the United States or a foreign country for the full term or terms for which the same may be granted, including all priority rights under the International Convention; and **ASSIGNOR** hereby authorizes and requests the United States Commissioner of Patents and Trademarks and any officials of foreign countries whose duty it is to issue patents on applications as aforesaid, to issue all patents for **THE ASSIGNED PATENT RIGHTS** to **ASSIGNEE** in accordance with the terms of this **ASSIGNMENT** but subject to reserved rights including but not limited to those previously retained by, granted to, or owned by, the United States government, educational institutions or both and hereby transfers and conveys all rights of action, power and benefit belonging to or accruing from **THE ASSIGNED PATENT RIGHTS** including the right to undertake proceedings to recover past and future damages and claim all other relief in respect of any acts of infringement thereof whether such acts shall have been committed before or after the date of this assignment.

No other rights, immunities, or licenses, including, without limitation, any rights to any intellectual property owned, controlled or licensable by **ASSIGNOR** are granted or assigned to **ASSIGNEE** under this **ASSIGNMENT**, either expressly or by implication, estoppel, or otherwise, other than the rights expressly recited herein.

ASSIGNOR hereby covenants that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would knowingly conflict with this Agreement;

ASSIGNOR further covenants that **ASSIGNEE** will, upon its lawful request, reasonably be provided with all pertinent facts and documents relating to **THE ASSIGNED PATENT RIGHTS** and legal equivalents as may be known and reasonably accessible to **ASSIGNOR** and that **ASSIGNOR** will testify as to the same in any administrative contest or litigation related thereto and will promptly execute and deliver to **ASSIGNEE** or its legal representative any and all papers, instruments or affidavits required to apply for, obtain, maintain, issue and enforce **THE ASSIGNED PATENT RIGHTS** and said equivalents in the United States or in any foreign country, which may be necessary or desirable to carry out the purposes thereof.

IN TESTIMONY WHEREOF, I hereunto set my hand as of the date indicated below.

SANDISK CORPORATION

Dated: 4th April 2011

Judy Bruner
Name: Judy Bruner
Title: EVP 2nd CFO

STATE OF California)
COUNTY OF Santa Clara) ss.

On this 4th day of April, 2011, before me Averil Branwen Watan (Notary Public), the undersigned Notary Public, personally appeared Judy Bruner,

who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.



Signature: Averil Watan
Signature of Notary Public

We accept the Assignment

SANDISK TECHNOLOGIES INC.

Dated: 4/4/11

James F. Brelsford
Name: James F. Brelsford
Title: President and Secretary

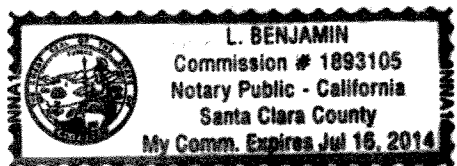
STATE OF California)
COUNTY OF Santa Clara) ss.

On this 4 day of April, 2011, before me L. Benjamin, the undersigned Notary Public, personally appeared JAMES F. BRELSFORD

who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.



Signature: L. Benjamin
Signature of Notary Public

Exhibit A

FILE #	INVENTORS	TITLE	COUNTRY	STATUS	SER #	FILING DATE	PAT #	ISSUE DATE
SDK0507.001US	Kevin Conley, Reuven Elhamias	Flash Controller Cache Architecture	US	Issued	11671394	5-Feb-07	7408834	5-Aug-08
SDK0507.002US	Kevin Conley, Reuven Elhamias	Flash Controller Cache Architecture	US	Published	12138708	13-Jun-08		
SDK0508.000US	Jeffrey Lutze, Tuan D. Pham, Masaaki Higashitani	Self Aligned Non-Volatile Memory Cells and Processes for Fabrication	US	Issued	10799060	12-Mar-04	7183153	27-Feb-07
SDK0508.001US	Jeffrey Lutze, Tuan D. Pham, Masaaki Higashitani	Self Aligned Non-Volatile Memory Cells and Processes for Fabrication	US	Issued	11622634	12-Jan-07	7436019	14-Oct-08
SDK0509.000US	Daniel Guterman	Programming Inhibit for Non-Volatile Memory	US	Issued	10823421	13-Apr-04	7170793	30-Jan-07
SDK0510.000US	Farookh Moogat, Yan Li	Partition of Non-Volatile Memory Array to Reduce Bit Line Capacitance	US	Issued	11078173	11-Mar-05	7313023	25-Dec-07
SDK0511.000US	Gerrit Jan Hemink, Yupin Fong	PROGRAMMING NON-VOLATILE MEMORY	US	Issued	10761620	21-Jan-04	6888758	3-May-05
SDK0511.001US	Gerrit Jan Hemink, Yupin Fong	PROGRAMMING NON-VOLATILE MEMORY	US	Issued	11081134	15-Mar-05	7035146	25-Apr-06
SDK0512.000US	John H Pasternak	Voltage Regulator with Bypass for Multi-Voltage Storage System	US	Issued	10633110	1-Aug-03	7212067	1-May-07
SDK0517.000US	Tuan D. Pham, Masaaki Higashitani	Low-Voltage, Multiple Thin-Gate Oxide and Low-Resistance Gate Electrode	US	Issued	11021693	22-Dec-04	7202125	10-Apr-07
SDK0518.000US	Masaaki Higashitani, Tuan D. Pham	Multi-Thickness Dielectric for Semiconductor Memory	US	Issued	11020402	22-Dec-04	7482223	27-Jan-09
SDK0520.000US	Sergey Anatolevich Gorobets	On-Chip Data Grouping and Alignment	US	Issued	11026549	30-Dec-04	7212440	1-May-07
SDK0520.001US	Sergey Anatolevich Gorobets	On-Chip Data Grouping and Alignment	US	Issued	11690253	21-Mar-07	7502259	10-Mar-09
SDK0521.000US	Sergey Anatolevich Gorobets, Yan Li	Pipelined Programming of Non-Volatile Memories Using Early Data	US	Issued	11013125	14-Dec-04	7120051	10-Oct-06
SDK0521.001US	Sergey Anatolevich Gorobets, Yan Li	Pipelined Programming of Non-Volatile Memories Using Early Data	US	Issued	11462946	7-Aug-06	7301805	27-Nov-07
SDK0522.000US	Sergey Anatolevich Gorobets	Erased Sector Detection Mechanisms	US	Issued	11020345	22-Dec-04	7437653	14-Oct-08
SDK0522.001US	Sergey Anatolevich Gorobets	Erased Sector Detection Mechanisms	US	Published	12208054	10-Sep-08		
SDK0523.000US	Raul-Adrian Cernea, Mehrdad Mofidi, Shahzad Khalid, Yan Li	Non-Volatile Memory And Method With Bit Line Compensation Dependent On Neighboring Operating Modes	US	Issued	10667223	17-Sep-03	6956770	18-Oct-05
SDK0523.001US	Raul-Adrian Cernea, Mehrdad Mofidi, Shahzad Khalid, Yan Li	Non-Volatile Memory And Method With Bit Line Compensation Dependent On Neighboring Operating Modes	US	Issued	11250357	13-Oct-05	7215574	8-May-07
SDK0524.000US	Alan Welsh Sinclair	Ring Bus Structure And it's Use In Flash Memory Systems	US	Published	10915039	9-Aug-04		
SDK0525.000US	Alan Welsh Sinclair	Disk Acceleration Using Frist and Second Storage Devices	US	Issued	10772789	4-Feb-04	7127549	24-Oct-06
SDK0525.001US	Alan Welsh Sinclair	Mass Storage Accelerator	US	Issued	11541013	29-Sep-06	7310699	18-Dec-07
SDK0527.000US	Jian Chen, Jeffrey Lutze, Kiran Ponnuru, Dat Tran, Jun Wan	Comprehensive Erase Verification for Non-Volatile Memory	US	Issued	10857245	28-May-04	7009889	7-Mar-06
SDK0527.001US	Dat Tran, Kiran Ponnuru, Jian Chen, Jeffrey Lutze, Jun Wan	Comprehensive Erase Verification for Non-Volatile Memory	US	Issued	11316069	21-Dec-05	7512014	31-Mar-09
SDK0527.002US	Dat Tran, Kiran Ponnuru, Jian Chen, Jeffrey Lutze, Jun Wan	Systems for Comprehensive Erase Verification for Non-Volatile Memory	US	Issued	11316475	21-Dec-05	7508720	24-Mar-09
SDK0527.003US	Dat Tran, Kiran Ponnuru, Jian Chen, Jeffrey Lutze, Jun Wan	Comprehensive Erase Verification for Non-Volatile Memory	US	Issued	11316119	21-Dec-05	7463532	9-Dec-08
SDK0527.004US	Dat Tran, Kiran Ponnuru, Jian Chen, Jeffrey Lutze, Jun Wan	SYSTEMS FOR COMPREHENSIVE ERASE VERIFICATION IN NON-VOLATILE MEMORY	US	Issued	11316162	21-Dec-05	7450435	11-Nov-08